

Form PTO-1449				Attorney Docket No. <b>062002-1752</b>		Serial No. <b>To Be Assigned</b>	
<b>INFORMATION DISCLOSURE CITATION</b>				Applicant <b>Martin, et al.</b>			
<i>(Use several sheets if necessary)</i>				Filing Date Even Date Herewith		Group <b>1763</b>	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initials	Item	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>WJP</i>	1A	1,712,407	5/7/1929	Skaupy			
<i>WJP</i>	1B	2,037,075	4/14/1936	Haines	250	27.5	
<i>WJP</i>	1C	3,304,456	2/14/1967	De Lany et al.	313	182	
<i>WJP</i>	1D	3,879,597	4/22/1975	Bersin et al.	219	121	
<i>WJP</i>	1E	4,031,424	6/21/1977	Penfold et al.	313	146	
<i>WJP</i>	1F	4,207,158	6/10/1980	Freeman	204	180	
<i>WJP</i>	1G	4,259,145	3/31/1981	Harper et al.	156	643	
<i>WJP</i>	1H	4,298,443	11/3/1981	Maydan	204	192	
<i>WJP</i>	1I	4,309,267	1/5/1982	Boyd et al.	204	298	
<i>WJP</i>	1J	4,450,787	5/29/1984	Weakliem et al.	118	723	
<i>WJP</i>	1K	4,464,223	<del>05/1999</del>	Gorin <i>08/1984</i>	438	729	
<i>WJP</i>	1L	4,496,881	1/29/1985	Cheever	315	357	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	1M						
	1N						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
<i>WJP</i>	1O	P. Breisacher et al. "Comparative Stabilities of Gaseous Alane, Gallane and Indane" Journal of the American Chemical Society pp. 4255-4258 87:19 Oct 5, 1965.					
<i>WJP</i>	1P	S. Veprek et al. "The Preparation of Thin Layers of Ge and Si by Chemical Hydrogen Plasma Transport." Solid-State Electronics Pergamon Press 1968 vol. 11 pp. 683-684.					
<i>WJP</i>	1Q	E. Wiberg et al "Hydrides of the Elements of Main Groups I-IV" New York 1971 Chapter 6 pp. 443-460.					
<i>WJP</i>	1R	A.P. Webb "Reactivity of Solid Silicon with Hydrogen Under Conditions of a Low Pressure Plasma." Chemical Physics Letters vol 62 No 1 Mar 15, 1979 pp 173-177.					
<i>WJP</i>	1W	S. Veprek et al. "Parameters Controlling the Deposition of Amorphous and Microcrystalline Silicon in Si/H Discharge Plasmas." Journal De Physique (Paris) 42 C4-251 (1981).					
* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							
EXAMINER'S SIGNATURE: <i>Maureen J. Chan</i>				DATE CONSIDERED: <i>6/4/2005</i>			

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U.S. PATENT DOCUMENTS							
Examiner Initials	Item	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MJP	4A	5,631,978	5/20/1997	Galand et al.	382	240	
MJP	4B	5,660,744	8/26/1997	Sekine et al.	219	121.43	
MJP	4C	5,882,538	3/16/1999	Martin et al.	216	71	
MJP	4D	5,890,102	3/30/1999	Kossentini et al.	702	181	
MJP	4E	5,906,684	05/19/99	Tamura et al.	118	728	
MJP	4F	5,917,285	6/29/1999	Gillis et al.	313	632	
MJP	4G	5,983,828	11/1999	Savas, Stephen E.	118	723	
MJP	4H	6,033,587	3/7/2000	Martin et al.	216	71	
MJP	4I	6,231,777	05/2001	Kofuji et al.	216	71	
MJP	4J	6,258,287	7/10/2001	Martin et al.	216	71	

  

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	4K						
	4L						

  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
MJP	4M	H.P. Gillis et al "Highly Anisotropic, Ultra-smooth Patterning of GaN/SiC by Low Energy Electron Enhanced Etching in DC Plasma" J. Electronic Mat 26, 301-305 (1997) pp 1-16.
	4N	
	4O	

  

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